

IN THE CLAIMS:

Please amend claims 1-6 as follows:

*Sub B1
03*

1. *(Once amended)* A vertical cavity surface emitting laser, comprising:
an active region further comprising at least one quantum well having a well depth of at least 40 meV and comprised of InGaAs and further including GaAs barrier layers sandwiching said at least one quantum well; and
GaAs confinement layers sandwiching said active region.
2. *(Once amended)* The vertical cavity surface emitting laser of claim 1 wherein said at least one quantum well is up to and including 50Å in thickness.
3. *(Once amended)* A vertical cavity surface emitting laser, comprising:
an active region further comprising at least one quantum well having a well depth of at least 40 meV and comprised of InGaAs and further including GaAsN barrier layers sandwiching said at least one quantum well; and
AlGaAs confinement layers sandwiching said active region.
4. *(Once amended)* The vertical cavity surface emitting laser of claim 3 wherein said at least one quantum well is up to and including 50Å in thickness.
5. *(Once amended)* A vertical cavity surface emitting laser, comprising:
an active region further comprising at least one quantum well having a well depth of at least 40 meV and comprised of InGaAs and further including AlGaAs barrier layers sandwiching said at least one quantum well; and
GaAsN confinement layers sandwiching said active region.
6. *(Once amended)* The vertical cavity surface emitting laser of claim 5 wherein said at least one quantum well is up to and including 50Å in thickness.